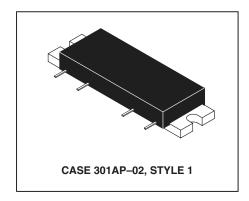
# The RF Line 3G Band RF Linear LDMOS Amplifier

Designed for ultra-linear amplifier applications in 50 ohm systems operating in the 3G frequency band. A silicon FET Class A design provides outstanding linearity and gain. In addition, the excellent group delay and phase linearity characteristics are ideal for digital CDMA modulation systems.

- Third Order Intercept: 45 dBm Typ
- Power Gain: 31 dB Typ (@ f = 2140 MHz)
- Excellent Phase Linearity and Group Delay Characteristics
- Ideal for Feedforward Base Station Applications

## MHL21336

2110-2170 MHz 3.0 W, 31 dB RF LINEAR LDMOS AMPLIFIER



### **ABSOLUTE MAXIMUM RATINGS** (T<sub>C</sub> = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit
DC Supply Voltage	$V_{DD}$	30	Vdc
RF Input Power	P <sub>in</sub>	+5	dBm
Storage Temperature Range	T <sub>stg</sub>	-40 to +100	°C
Operating Case Temperature Range	T <sub>C</sub>	-20 to +100	°C

### ELECTRICAL CHARACTERISTICS (V<sub>DD</sub> = 26 Vdc, T<sub>C</sub> = 25°C; 50 Ω System)

Characteristic	;	Symbol	Min	Тур	Max	Unit
Supply Current		I <sub>DD</sub>	_	500	525	mA
Power Gain	(f = 2140 MHz)	Gp	30	31	32	dB
Gain Flatness	(f = 2110-2170 MHz)	G <sub>F</sub>	_	0.15	0.4	dB
Power Output @ 1 dB Comp.	(f = 2140 MHz)	P <sub>out</sub> 1 dB	34	35	_	dBm
Input VSWR	(f = 2110–2170 MHz)	VSWR <sub>in</sub>	_	1.2:1	1.5:1	
Third Order Intercept (f1 = 2137 MHz, f2 = 2142 MHz)		ITO	44	45	_	dBm
Noise Figure	(f = 2170 MHz)	NF	_	4.5	5	dB



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### TYPICAL CHARACTERISTICS

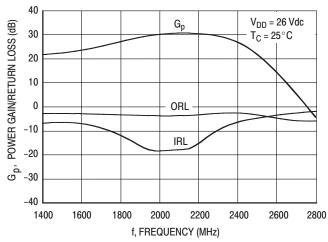


Figure 1. Power Gain, Input Return Loss, **Output Return Loss versus Frequency** 

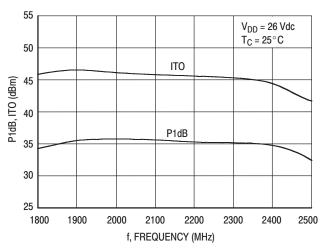


Figure 2. P1dB, ITO versus Frequency

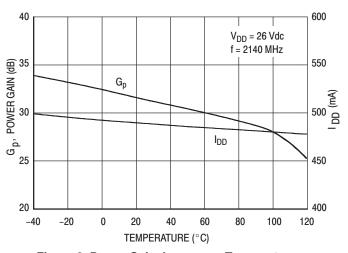


Figure 3. Power Gain, I<sub>DD</sub> versus Temperature

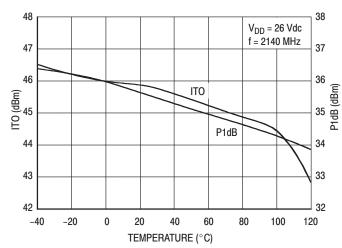


Figure 4. ITO, P1dB versus Temperature

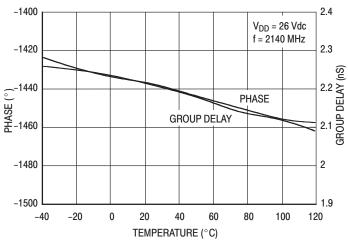


Figure 5. Phase<sup>(1)</sup>, Group Delay<sup>(1)</sup> versus **Temperature** 

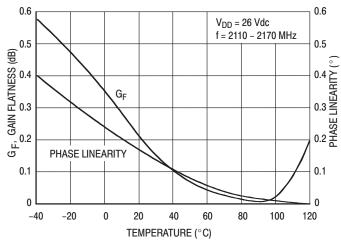


Figure 6. Gain Flatness, Phase Linearity versus Temperature

(1)In Production Test Fixture

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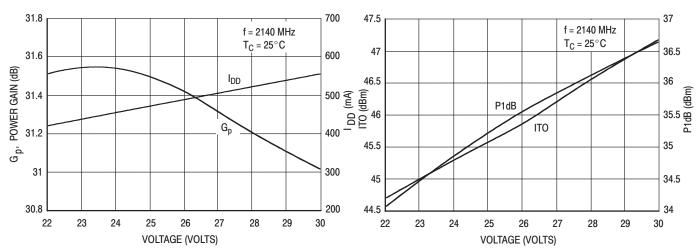


Figure 7. Power Gain, I<sub>DD</sub> versus Voltage

Figure 8. ITO, P1dB versus Voltage

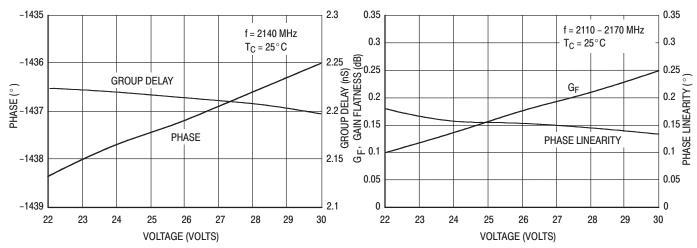


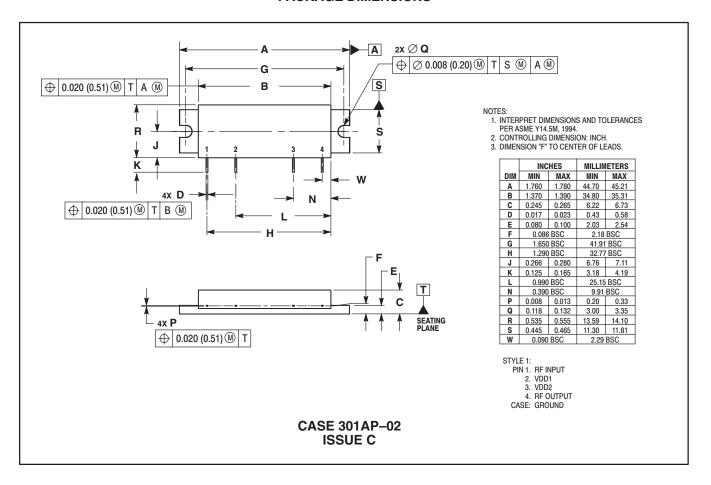
Figure 9. Phase<sup>(1)</sup>, Group Delay<sup>(1)</sup> versus
Voltage

(1)In Production Test Fixture

Figure 10. Phase Linearity, Gain Flatness versus Voltage

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### PACKAGE DIMENSIONS



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